VHF POWER MOSFET
Silicon N-Channel Enhancement Mode

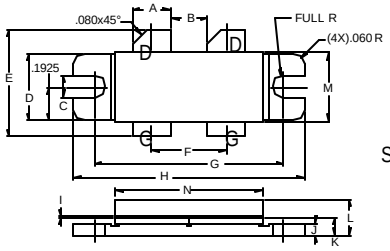
DESCRIPTION:

The **VFT300-28** is Designed for Wideband High Power VHF Amplifier Applications operating up to 250 MHz.

FEATURES:

- P_G = 14 dB Typical at 175 MHz
- η_D = 55% Typ. at P_{OUT} = 300 Watts
- ***Omnigold***™ Metalization System

PACKAGE STYLE .400 BAL FLG (D)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.210 / 5.33	
C	.125 / 3.18	
D	.380 / 9.65	.390 / 9.91
E	.580 / 14.73	.620 / 15.75
F	.435 / 11.05	
G	1.090 / 27.69	1.105 / 28.07
H	1.335 / 33.91	1.345 / 34.16
I	.003 / 0.08	.007 / 0.18
J	.060 / 1.52	.070 / 1.78
K	.100 / 2.54	.115 / 2.92
L		.230 / 5.84
M	.395 / 10.03	.407 / 10.34
N	.850 / 21.59	.870 / 22.10

ORDER CODE: ASI10707

MAXIMUM RATINGS

I_D	16 A
$V_{(BR)DSS}$	65 V
V_{DGR}	65 V
V_{GS}	± 40 V
P_{DISS}	300 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.6 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	V_{GS} = 0 V	I_{DS} = 100 mA		65			V
I_{DSS}	V_{DS} = 28 V	V_{GS} = 0 V				5.0	mA
I_{GSS}	V_{DS} = 0 V	V_{GS} = 20 V				1.0	μA
V_{GS}	V_{DS} = 10 V	I_D = 100 mA		1.0		5.0	V
V_{DS}	V_{GS} = 10 V	I_D = 10 A				1.5	V
G_{FS}	V_{DS} = 10 V	I_D = 5 A		3500			mS
C_{iss} C_{oss} C_{rss}	V_{GS} = 28 V	V_{DS} = 0 V	F = 1.0 MHz		375 188 26		pF
G_{PS} η_D	V_{DD} = 28 V f = 175 MHz	I_{DQ} = 2 x 250 mA	P_{OUT} = 300 W	12 50	14 55		dB %

Specifications are subject to change without notice.

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